

## N-Channel Enhancement Mode Power MOSFET

## Description

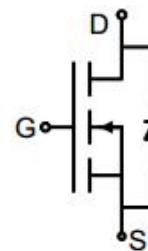
The GT800N10I uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. It can be used in a wide variety of applications.

## General Features

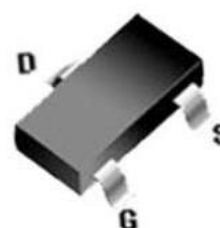
- $V_{DS}$  100V
- $I_D$  (at  $V_{GS} = 10V$ ) 3.4A
- $R_{DS(ON)}$  (at  $V_{GS} = 10V$ ) < 80m $\Omega$
- $R_{DS(ON)}$  (at  $V_{GS} = 4.5V$ ) < 100m $\Omega$
- 100% Avalanche Tested
- RoHS Compliant

## Application

- Power switch
- DC/DC converters



Schematic diagram



SOT-23

## Ordering Information

| Device    | Package | Marking  | Packaging    |
|-----------|---------|----------|--------------|
| GT800N10I | SOT-23  | GT800N10 | 3000pcs/Reel |

Absolute Maximum Ratings  $T_C = 25^\circ\text{C}$ , unless otherwise noted

| Parameter                                        | Symbol         | Value      | Unit             |
|--------------------------------------------------|----------------|------------|------------------|
| Drain-Source Voltage                             | $V_{DS}$       | 100        | V                |
| Continuous Drain Current                         | $I_D$          | 3.4        | A                |
| Pulsed Drain Current (note1)                     | $I_{DM}$       | 13.6       | A                |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$   | V                |
| Power Dissipation                                | $P_D$          | 1.7        | W                |
| Single pulse avalanche energy (note2)            | $E_{AS}$       | 6          | mJ               |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | -55 To 150 | $^\circ\text{C}$ |

## Thermal Resistance

| Parameter                                             | Symbol     | Value | Unit               |
|-------------------------------------------------------|------------|-------|--------------------|
| Thermal Resistance, Junction-to-Ambient, $t \leq 10s$ | $R_{thJA}$ | 73.5  | $^\circ\text{C/W}$ |

| Specifications T <sub>J</sub> = 25°C, unless otherwise noted |                      |                                                                         |       |      |      |      |
|--------------------------------------------------------------|----------------------|-------------------------------------------------------------------------|-------|------|------|------|
| Parameter                                                    | Symbol               | Test Conditions                                                         | Value |      |      | Unit |
|                                                              |                      |                                                                         | Min.  | Typ. | Max. |      |
| Static Parameters                                            |                      |                                                                         |       |      |      |      |
| Drain-Source Breakdown Voltage                               | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                            | 100   | --   | --   | V    |
| Zero Gate Voltage Drain Current                              | I <sub>DSS</sub>     | V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V                            | --    | --   | 1    | μA   |
| Gate-Source Leakage                                          | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20V                                                  | --    | --   | ±100 | nA   |
| Gate-Source Threshold Voltage                                | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA              | 1.0   | 1.9  | 2.5  | V    |
| Drain-Source On-Resistance                                   | R <sub>DS(on)</sub>  | V <sub>GS</sub> = 10V, I <sub>D</sub> = 2A                              | --    | 67   | 80   | mΩ   |
|                                                              |                      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2A                             | --    | 84   | 100  |      |
| Forward Transconductance                                     | g <sub>FS</sub>      | V <sub>GS</sub> = 5V, I <sub>D</sub> = 2A                               | --    | 3    | --   | S    |
| Dynamic Parameters                                           |                      |                                                                         |       |      |      |      |
| Input Capacitance                                            | C <sub>iss</sub>     | V <sub>GS</sub> = 0V,<br>V <sub>DS</sub> = 50V,<br>f = 1.0MHz           | --    | 210  | --   | pF   |
| Output Capacitance                                           | C <sub>oss</sub>     |                                                                         | --    | 70   | --   |      |
| Reverse Transfer Capacitance                                 | C <sub>rss</sub>     |                                                                         | --    | 3    | --   |      |
| Total Gate Charge                                            | Q <sub>g</sub>       | V <sub>DD</sub> = 50V,<br>I <sub>D</sub> = 2A,<br>V <sub>GS</sub> = 10V | --    | 5    | --   | nC   |
| Gate-Source Charge                                           | Q <sub>gs</sub>      |                                                                         | --    | 2    | --   |      |
| Gate-Drain Charge                                            | Q <sub>gd</sub>      |                                                                         | --    | 1    | --   |      |
| Turn-on Delay Time                                           | t <sub>d(on)</sub>   | V <sub>DD</sub> = 50V,<br>I <sub>D</sub> = 2A,<br>R <sub>G</sub> = 2Ω   | --    | 15   | --   | ns   |
| Turn-on Rise Time                                            | t <sub>r</sub>       |                                                                         | --    | 4    | --   |      |
| Turn-off Delay Time                                          | t <sub>d(off)</sub>  |                                                                         | --    | 21   | --   |      |
| Turn-off Fall Time                                           | t <sub>f</sub>       |                                                                         | --    | 3    | --   |      |
| Drain-Source Body Diode Characteristics                      |                      |                                                                         |       |      |      |      |
| Continuous Body Diode Current                                | I <sub>S</sub>       | T <sub>C</sub> = 25°C                                                   | --    | --   | 3.4  | A    |
| Body Diode Voltage                                           | V <sub>SD</sub>      | T <sub>J</sub> = 25°C, I <sub>SD</sub> = 2A, V <sub>GS</sub> = 0V       | --    | --   | 1.2  | V    |
| Reverse Recovery Charge                                      | Q <sub>rr</sub>      | I <sub>F</sub> = 2A, V <sub>GS</sub> = 0V<br>di/dt=100A/us              | --    | 40   | --   | nC   |
| Reverse Recovery Time                                        | T <sub>rr</sub>      |                                                                         | --    | 33   | --   | ns   |

## Notes

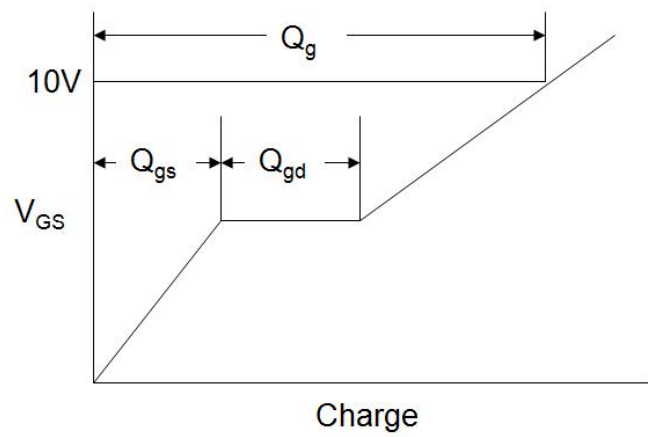
1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. EAS condition :  $T_J = 25^\circ\text{C}, V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$

The table shows the minimum avalanche energy, which is 16mJ when the device is tested until failure

3. Identical low side and high side switch with identical  $R_G$

### Gate Charge Test Circuit



### Switch Time Test Circuit

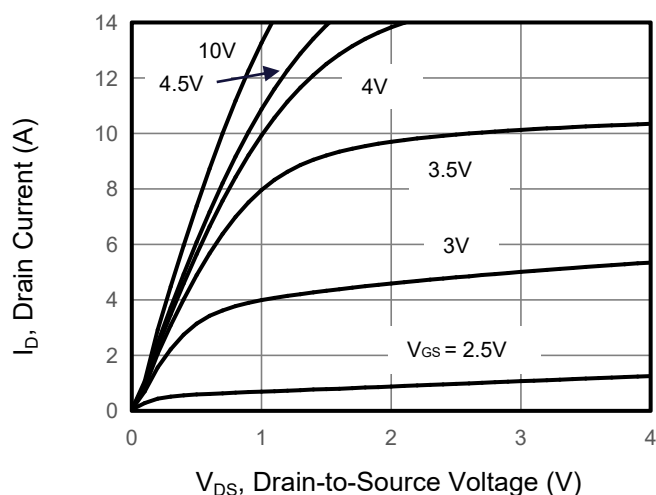


### EAS Test Circuit

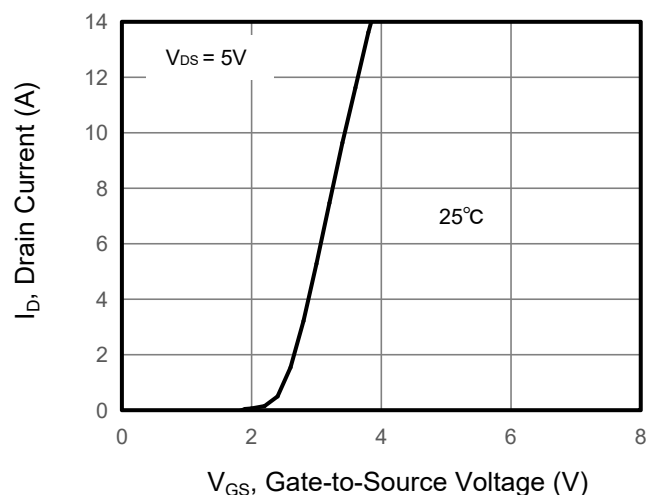


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

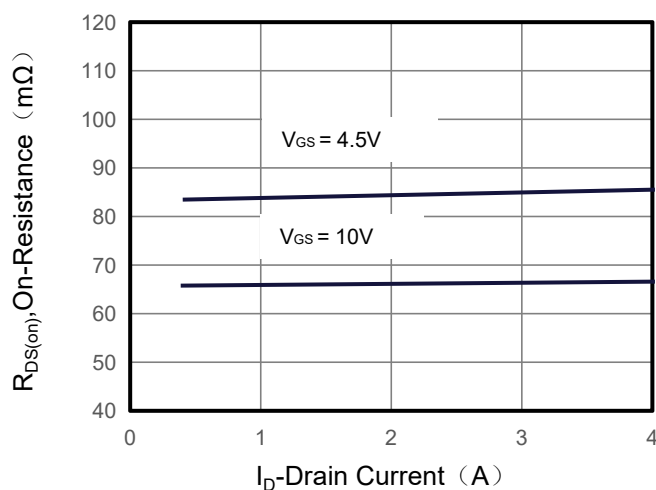
**Figure 1. Output Characteristics**



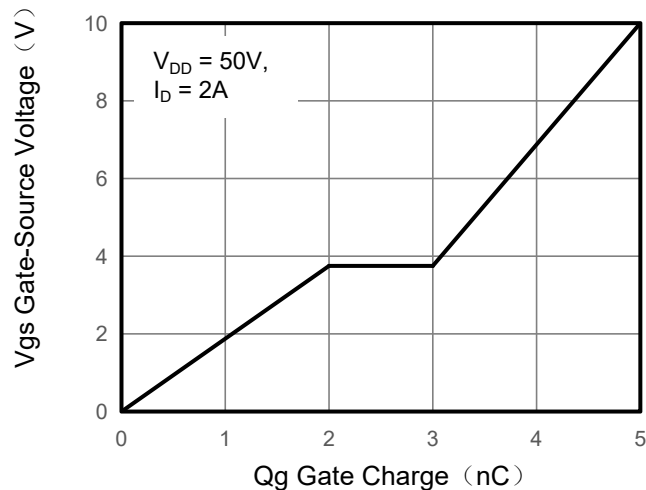
**Figure 2. Transfer Characteristics**



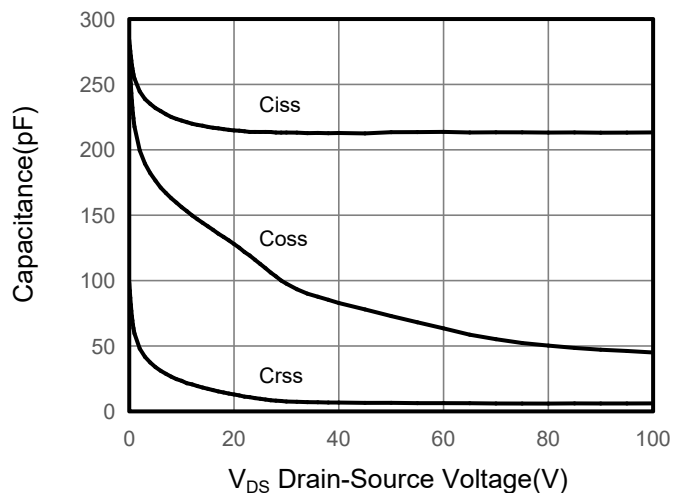
**Figure 3. Drain Source On Resistance**



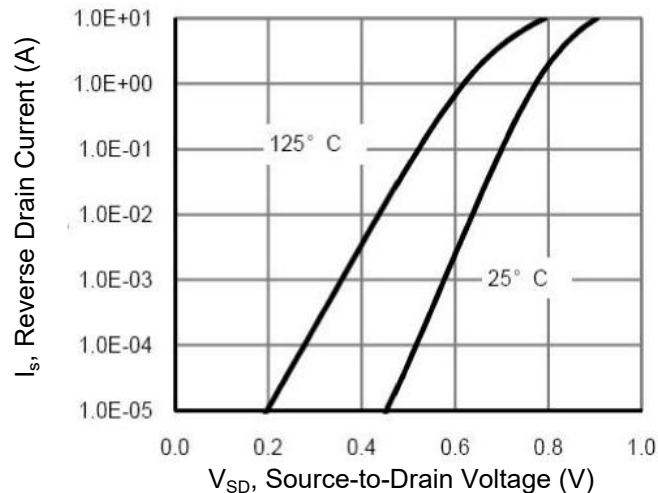
**Figure 4. Gate Charge**



**Figure 5. Capacitance**

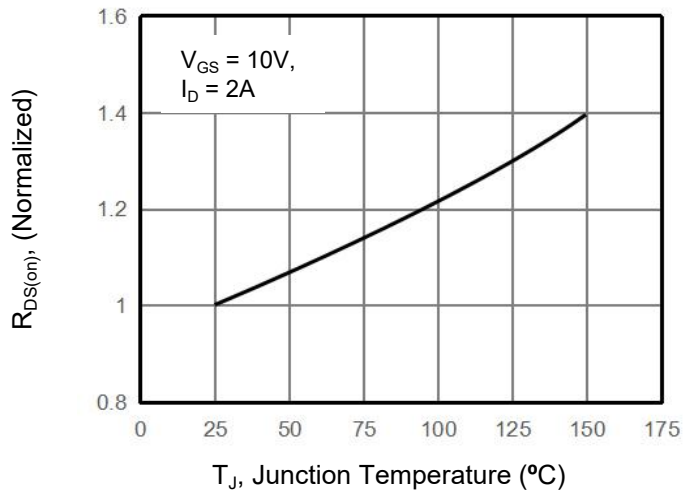


**Figure 6. Source-Drain Diode Forward**

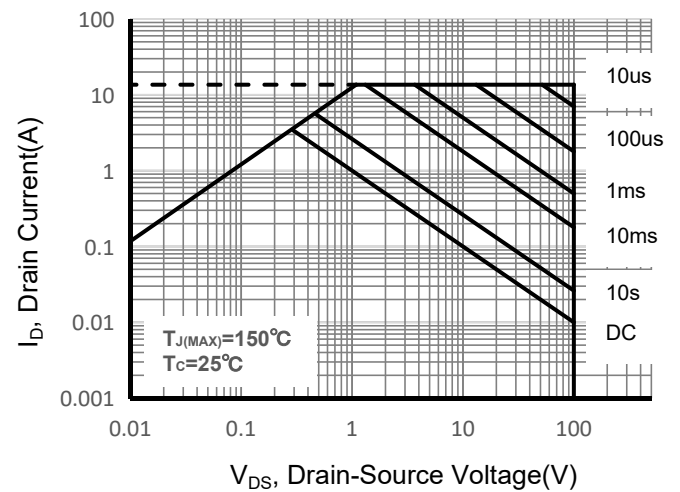


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

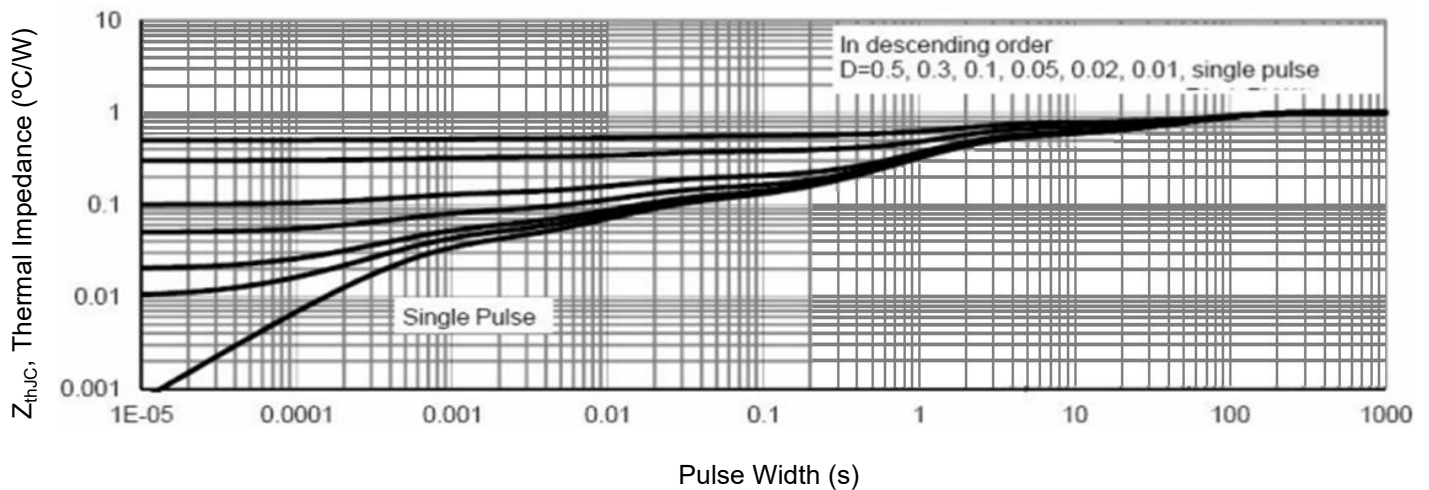
**Figure 7. Drain-Source On-Resistance**



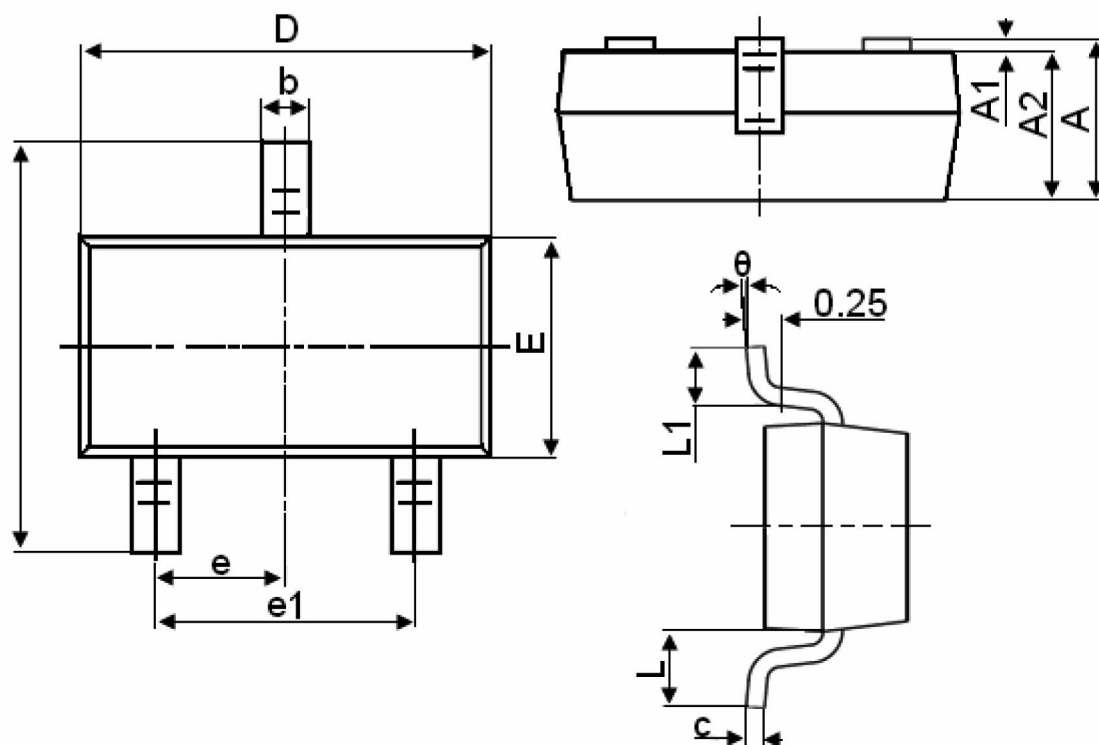
**Figure 8. Safe Operation Area**



**Figure 9. Normalized Maximum Transient Thermal Impedance**



## SOT-23 Package Information



| Symbol   | Dimensions in Millimeters |       |
|----------|---------------------------|-------|
|          | MIN.                      | MAX.  |
| A        | 0.900                     | 1.150 |
| A1       | 0.000                     | 0.100 |
| A2       | 0.900                     | 1.050 |
| b        | 0.300                     | 0.500 |
| c        | 0.080                     | 0.150 |
| D        | 2.800                     | 3.000 |
| E        | 1.200                     | 1.400 |
| E1       | 2.250                     | 2.550 |
| e        | 0.950TYP                  |       |
| e1       | 1.800                     | 2.000 |
| L        | 0.550REF                  |       |
| L1       | 0.300                     | 0.500 |
| $\theta$ | 0°                        | 8°    |